

VL5010 DEVICE MODELING – II

DETAILED SYLLBUS

OBJECTIVES:

- To understand device physics and device modelling aspects
- To study simulators to characterize the device models

UNIT I MOSFET DEVICE PHYSICS

MOSFET Basic operation, Level 1, Level 2, Level 3 models, Noise sources in MOSFET, Flicker noise modeling, Thermal noise modelling, Influence of process variation, modeling of device mismatch for Analog/RF Applications

UNIT II DEVICE MODELLING

Prime importance of circuit and device simulations in VLSI; Nodal, mesh, modified nodal and hybrid analysis equations. Solution of network equations: Sparse matrix techniques, solution of nonlinear networks through Newton-Raphson technique, convergence and stability.

UNIT III MULTISTEP METHODS

Solution of stiff systems of equations, adaptation of multistep methods to the solution of electrical networks, general purpose circuit simulators.

UNIT IV MATHEMATICAL TECHNIQUES FOR DEVICE SIMULATIONS

Poisson equation, continuity equation, drift-diffusion equation, Schrodinger equation, hydrodynamic equations, trap rate, finite difference solutions to these equations in 1D and 2D space, grid generation.

UNIT V SIMULATION OF DEVICES

Computation of characteristics of simple devices like p-n junction, MOS capacitor and MOSFET; Small-signal analysis.

REFERENCES:

1. Arora, N., "MOSFET Models for VLSI Circuit Simulation", Springer-Verlag, 1993
2. Chua, L.O. and Lin, P.M., "Computer-Aided Analysis of Electronic Circuits: Algorithms and Computational Techniques", Prentice-Hall., 1975
3. Fjeldly, T., Ytterdal, T. and Shur, M., "Introduction to Device Modeling and Circuit Simulation", Wiley-Interscience., 1997
4. Grasser, T., "Advanced Device Modeling and Simulation", World Scientific Publishing Company., 2003
5. Selberherr, S., "Analysis and Simulation of Semiconductor Devices", Springer-Verlag., 1984
6. Trond Ytterdal, Yuhua Cheng and Tor A. FjeldlyWayne Wolf, "Device Modeling for Analog and RF CMOS Circuit Design", John Wiley & Sons Ltd.